

2N5551

NPN SILICON TRANSISTOR

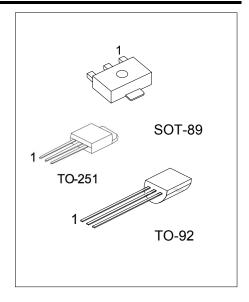
HIGH VOLTAGE SWITCHING TRANSISTOR

■ FEATURES

- * High collector-emitter voltage: V_{CEO}=160V
- * High current gain

■ APPLICATIONS

- * Telephone switching circuit
- * Amplifier



ORDERING INFORMATION

Ordering Number			Dookogo	Pin Assignment			Dooking	
Normal	Lead Free Plating	Halogen Free	Package	1	2	3	Packing	
2N5551-x-AB3-R	2N5551L-x-AB3-R	2N5551G-x-AB3-R	SOT-89	В	С	Е	Tape Reel	
2N5551-x-T92-B	2N5551L-x-T92-B	2N5551G-x-T92-B	TO-92	Е	В	O	Tape Box	
2N5551-x-251-K	2N5551L-x-251-K	2N5551G-x-251	TO-251	Е	В	С	Tube	



■ ABSOLUTE MAXIMUM RATINGS (Ta=25°C, unless otherwise specified)

PARAMETER			RATINGS	UNIT
Collector-Base Voltage		V_{CBO}	180	V
Collector-Emitter Voltage		V_{CEO}	160	V
Emitter-Base Voltage		V_{EBO}	6	V
Collector Dissipation T	TO-92	В	625	mW
Collector Dissipation S	SOT-89	Pc	500	mW
Collector Current		Ic	600	mA
Junction Temperature		T_J	+150	$^{\circ}\!\mathbb{C}$
Storage Temperature		T _{STG}	-55 ~ +150	$^{\circ}$

Note: Absolute maximum ratings are those values beyond which the device could be permanently damaged. Absolute maximum ratings are stress ratings only and functional device operation is not implied.

■ ELECTRICAL CHARACTERISTICS (Ta=25°C, unless otherwise specified)

PARAMETER	SYMBOL	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Collector-Base Breakdown Voltage	BV _{CBO}	$I_C=100\mu A, I_E=0$	180			V
Collector-Emitter Breakdown Voltage	BV _{CEO}	I _C =1mA, I _B =0	160			V
Emitter-Base Breakdown Voltage	BV _{EBO}	$I_E=10\mu A, I_C=0$	6			V
Collector Cut-off Current	I _{CBO}	V _{CB} =120V, I _E =0			50	nA
Emitter Cut-off Current	I _{EBO}	V_{BE} =4 V , I_{C} =0			50	nA
	h _{FE1}	V _{CE} =5V, I _C =1mA	80			
DC Current Gain(Note)	h _{FE2}	V _{CE} =5V, I _C =10mA	80	160	400	
	h _{FE3}	V _{CE} =5V, I _C =50mA	80			
Collector-Emitter Saturation Voltage	\ \/	I _C =10mA, I _B =1mA			0.15	V
Collector-Emitter Saturation Voltage	V _{CE(SAT)}	I _C =50mA, I _B =5mA			0.2	V
Base-Emitter Saturation Voltage	VDE(CAT)	I _C =10mA, I _B =1mA			1	V
Base-Emilier Saturation voltage		I _C =50mA, I _B =5mA			1	V
Current Gain Bandwidth Product f _T		V _{CE} =10V, I _C =10mA, f=100MHz	100		300	MHz
Output Capacitance Cob		V _{CB} =10V, I _E =0 f=1MHz			6.0	pF
Noise Figure	NF	I _C =0.25mA, V _{CE} =5V			0	40
Noise Figure		R_S =1k Ω , f=10Hz ~ 15.7kHz			8	dB

Note: Pulse test: PW<300µs, Duty cycle<2%

■ CLASSIFICATION OF h_{FE}

RANK	А	В	С		
RANGE	80-170	150-240	200-400		



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■ TYPICAL CHARACTERISTICS

